



PRODUCT NAME : 2N3703 PNP General Purpose Transistor (Pack of 5)

PRICE : Rs 20.00

SKU : RM2043



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DESCRIPTION

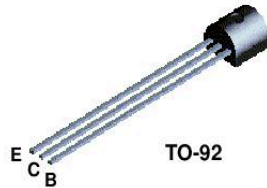
Features

- Collector-Emitter Volt (V_{ce0}): 30V
- Collector-Base Volt (V_{cb0}): 50V
- Collector Current (I_c): 0.5A
- h_{fe} : 30-150 @ 50mA
- Power Dissipation (P_{tot}): 625mW
- Current-Gain-Bandwidth (f_{total}): 100MHz
- Type: PNP



*Discrete POWER & Signal
Technologies*

2N3703



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N3703	
P_D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

2N3703

PNP General Purpose Amplifier
(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10\text{ mA}, I_B = 0$	30		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\text{ }\mu\text{A}, I_E = 0$	50		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100\text{ }\mu\text{A}, I_C = 0$	5.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 20\text{ V}, I_E = 0$		100	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0\text{ V}, I_C = 0$		100	nA

ON CHARACTERISTICS*

h_{FE}	DC Current Gain	$V_{CE} = 5.0\text{ V}, I_C = 50\text{ mA}$	30	150	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 50\text{ mA}, I_B = 5.0\text{ mA}$		0.25	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 5.0\text{ V}, I_C = 50\text{ mA}$	0.6	1.0	V

SMALL SIGNAL CHARACTERISTICS

C_{ob}	Output Capacitance	$V_{CB} = 10\text{ V}, f = 1.0\text{ MHz}$		12	pF
f_T	Current Gain - Bandwidth Product	$I_C = 50\text{ mA}, V_{CE} = 5.0\text{ V}, f = 20\text{ MHz}$	100		MHz

* Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

